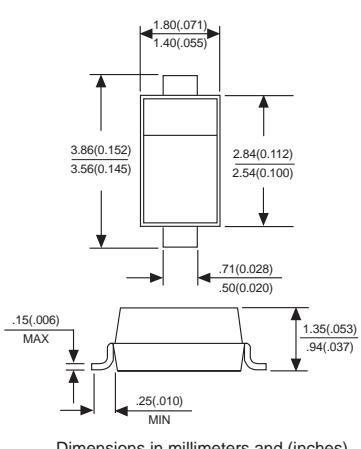


SCHOTTKY DIODES						
SOD-123  <p>Dimensions in millimeters and (inches)</p>		Features Low forward voltage drop Guard ring construction for transient protection Negligible reverse recovery time low reverse capacitance				
		Mechanical Data Case: Molded plastic body Terminals: Plated leads solderable per MIL-STD-750, Method 2026 Polarity: Polarity symbols marked on case Mounting Position: Any Marking: SD103AW:S4, SD103BW:S5, SD103CW:S6				
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS						
Maximum ratings and electrical characteristics, Single diode @ $T_A=25^\circ C$						
PARAMETER	SYMBOLS	SD103AW	SD103BW	SD103CW	UNITS	
Peak repetitive peak reverse voltage	V_{RRM}					
Working peak reverse voltage	V_{RWM}	40	30	20	VOLTS	
DC Blocking voltage	V_{DC}					
RMS Reverse voltage	$V_{R(RMS)}$	28	21	14	V	
Forward continuous current	I_{FM}		350			mA
Repetitive peak forward current @ $t \leq 1.0s$	I_{FRM}		1.5			A
Power dissipation	P_d		400			mW
Thermal resistance junction to ambient	$R_{\Theta JA}$		300			°C/W
Storage temperature	T_{STG}		-65 to +125			°C
Electrical ratings @ $T_A=25^\circ C$						
PARAMETER	SYMBOLS	Min.	Typ.	Max.	Unit	Conditions
Reverse breakdown voltage SD103AW SD103BW SD103CW	$V_{(BR)R}$	40 30 20			V	$I_R=100\mu A$ $I_R=100\mu A$ $I_R=100\mu A$
Forward voltage	V_F			0.37 0.60	V	$I_F=20mA$ $I_F=200mA$
Reverse current SD103AW SD103BW SD103CW	I_{RM}			5.0	uA	$V_R=30V$ $V_R=20V$ $V_R=10V$
Capacitance between terminals	C_T		50		pF	$V_R=0V, f=1.0MHz$
Reverse recovery time	t_{rr}		10		ns	$I_F=I_R=200mA$ $I_{rr}=0.1XI_R, R_L=100\Omega$

RATINGS AND CHARACTERISTIC CURVES SD103AW-SD103CW

FIG. 1- TYPICAL FORWARD CHARACTERISTICS

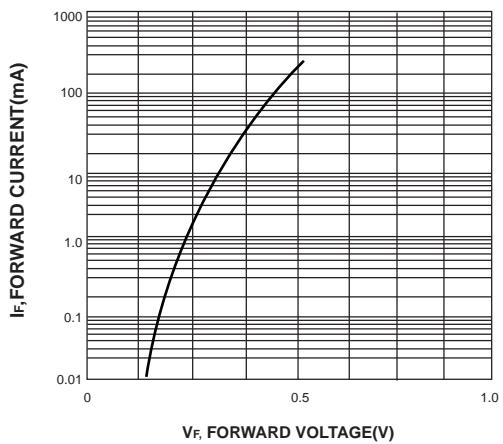


FIG. 2-TYP. JUNCTION CAPACITANCE VS REVERSE VOLTAGE

